



MMBT4401

NPN GENERAL PURPOSE SWITCHING TRANSISTOR

VOLTAGE 40 Volts **POWER** 225 mWatts

SOT-23 Unit: inch (mm)

FEATURES

- NPN epitaxial silicon, planar design
- Collector-emitter voltage $V_{CE} = 40V$
- Collector current $I_C = 600mA$
- In compliance with EU RoHS 2002/95/EC directives

MECHANICAL DATA

- Case: SOT-23, Plastic
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.008 gram
- Marking: M4A

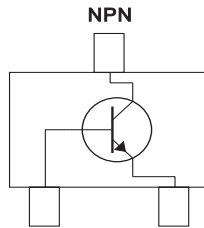
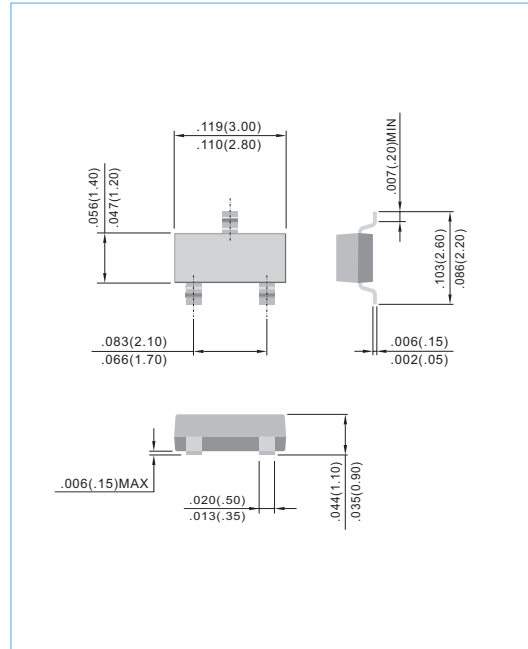


Fig.34

ABSOLUTE RATINGS

PARAMETER	Symbol	Value	Units
Collector - Emitter Voltage	V_{CEO}	40	V
Collector - Base Voltage	V_{CBO}	60	V
Emitter - Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous	I_C	600	mA

THERMAL CHARACTERISTICS

PARAMETER	Symbol	Value	Units
Max Power Dissipation (Note 1)	P_{TOT}	225	mW
Thermal Resistance , Junction to Ambient	$R_{\theta A}$	556	$^{\circ}C/W$
Junction Temperature	T_J	-55 to 150	$^{\circ}C$
Storage Temperature	T_{STG}	-55 to 150	$^{\circ}C$

Note 1: Transistor mounted on FR-5 board 1.0 x 0.75 x 0.062 in.



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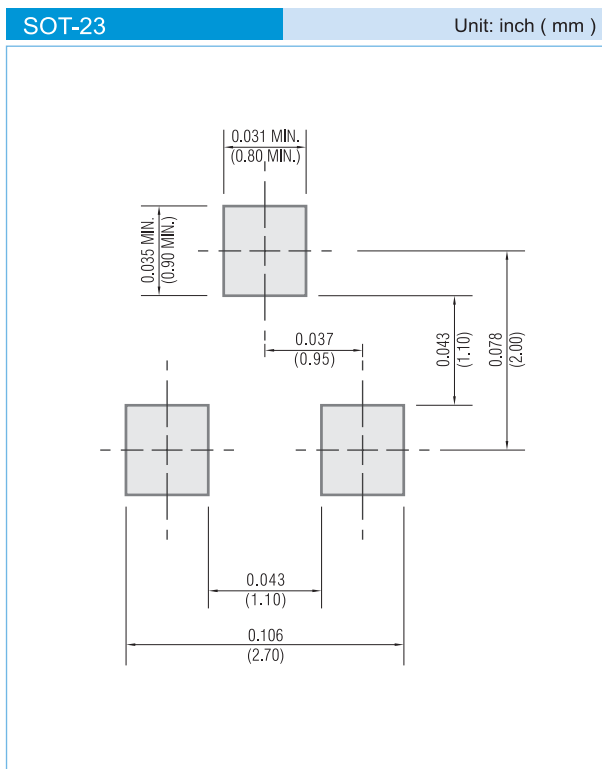
ELECTRICAL CHARACTERISTICS

PARAMETER	Symbol	Test Condition	MIN.	TYP.	MAX.	Units
Collector - Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=1.0mA, I_B=0$	40	-	-	V
Collector - Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	60	-	-	V
Emitter - Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	6.0	-	-	V
Base Cutoff Current	I_{BL}	$V_{CE}=35V, V_{EB}=0.4V$	-	-	100	nA
Collector Cutoff Current	I_{CEX}	$V_{CE}=35V, V_{EB}=0.4V$	-	-	100	nA
DC Current Gain (Note 2)	h_{FE}	$I_C=0.1mA, V_{CE}=1.0V$	20	-	-	-
		$I_C=1.0mA, V_{CE}=1.0V$	40	-	-	
		$I_C=10mA, V_{CE}=1.0V$	80	-	-	
		$I_C=150mA, V_{CE}=1.0V$	100	-	300	
		$I_C=500mA, V_{CE}=2.0V$	40	-	-	
Collector - Emitter Saturation Voltage (Note 2)	$V_{CE(SAT)}$	$I_C=150mA, I_B=15mA$ $I_C=500mA, I_B=50mA$	-	-	0.40 0.75	V
Base - Emitter Saturation Voltage (Note 2)	$V_{BE(SAT)}$	$I_C=150mA, I_B=15mA$ $I_C=500mA, I_B=50mA$	0.75 -	- -	0.95 1.20	V
Collector - Base Capacitance	C_{CBO}	$V_{CB}=5V, I_E=0, f=1MHz$	-	-	6.5	pF
Emitter - Base Capacitance	C_{EBO}	$V_{CB}=0.5V, I_C=0, f=1MHz$	-	-	30	pF
Current Gain - Bandwidth Product	F_T	$V_{CE}=10V, I_C=20mA, f=100MHz$	250	-	-	MHz
Delay Time	t_d	$V_{CC}=30V, V_{BE}=2.0V,$ $I_C=150mA, I_{B1}=15mA$	-	-	15	ns
Rise Time	t_r	$V_{CC}=30V, V_{BE}=2.0V,$ $I_C=150mA, I_{B1}=15mA$	-	-	20	ns
Storage Time	t_s	$V_{CC}=30V, I_C=150mA$ $I_{B1}=I_{B2}=15mA$	-	-	225	ns
Fall Time	t_f	$V_{CC}=30V, I_C=150mA$ $I_{B1}=I_{B2}=15mA$	-	-	30	ns



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MOUNTING PAD LAYOUT



ORDER INFORMATION

- Packing information
 - T/R - 12K per 13" plastic Reel
 - T/R - 3K per 7" plastic Reel

LEGAL STATEMENT

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